

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device, comprising:
 - a first substrate formed of an insulating material having at least one through hole;
 - a semiconductor element secured to a desired position of a conductive pattern formed on a first main surface of said first substrate;
 - a metal wire for electrically connecting an electrode pad of said semiconductor element to said desired conductive pattern;
 - a plurality of electrodes for external connection on a second main surface of said first substrate located opposite to the first main surface of said first substrate that is electrically connected to said desired conductive pattern via said through hole;
 - a resin mold formed so as to cover, at least, the main surfaces of said first substrate, wherein
 - the semiconductor device is characterized in that a second substrate formed of an insulating material having approximately the same coefficient of linear expansion as said first substrate is adhered to the second main surface of said first substrate so that, at least, said electrodes for external connection are exposed.
2. (Original) The semiconductor device according to Claim 1, characterized in that said second substrate is adhered to said first substrate so that, at least, the sides of said electrodes for external connection located in the vicinity of the outer sides of the second main surface of said first substrate are exposed from said outer sides.

3. (Currently Amended) The semiconductor device according to Claim 1 or 2, characterized in that said second substrate separates from each other said electrodes for external connection on the second main surface of said first substrate so that the electrodes exist independently in separate regions.

4. (Currently Amended) The semiconductor device according to Claim 2 or 3, characterized in that said second substrate is thicker than said electrodes for external connection.

5. (Currently Amended) The semiconductor device according to Claim 2 or 3, characterized in that said electrodes for external connection are plated with gold.

6. (Currently Amended) The semiconductor device according to Claim 2 or 3, characterized in that said first and second substrates are ceramic substrates.

7. (New) The semiconductor device according to Claim 2, characterized in that said second substrate separates from each other said electrodes for external connection on the second main surface of said first substrate so that the electrodes exist independently in separate regions.

8. (New) The semiconductor device according to Claim 3, characterized in that said second substrate is thicker than said electrodes for external connection.

9. (New) The semiconductor device according to Claim 3, characterized in that said electrodes for external connection are plated with gold.

10. (New) The semiconductor device according to Claim 3, characterized in that said first and second substrates are ceramic substrates